

LEAST: 10/22/2003 10:01:41 AM [F00135891]

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23 with 24

Feb. 2005

L23: (164) 19 near 22

L24: (918648) gate

L25: (10104) (charge near 3 (strap\$4 trap\$4 nitride))

L27: (0) 23 with 25

L28: (329) 19 with 22

L29: (0) 28 with 25

L30: (0) 28 same 25

L28: (21) 23 with 24

L31: (27) 28 and 25

Failed

(silicon adj dioxide) SiO "SiO.sub.2"

Saved

S2: (1) 09/948877

S3: (1736) "KONINKLIJKE PHILIPS" as.

S1: (0) 10/753914

S4: (2) "6750066" PN.

S5: (0) 10/775908

S6: (730) NROM

S7: (282591) (silicon adj dioxide SiO "SiO.sub.2")

S8: (100381) (dielectric adj constant relative adj (permittivit\$3 permittiv

S9: (98333) (dielectric adj constant relative adj (permittivit\$3 permittiv\$

S10: (4349) high adj k

S11: (25178) high near S9

S12: (28017) S10 S11

Doc: US POPULAR LIT. EPO JPN DERIVENT. BM TCB

Transl. source: JPN

	U	Inventor	Document	Issue	P	Title	Current	Current X	Retrieval	S	C	P	Image	Do	P
1	<input type="checkbox"/>	Lei, Tan Fu	US 200401	2004	9	Process of utilizing CF4 plasma pretre	438/28	438/591		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
2	<input type="checkbox"/>	Paranjpe, A	US 200300	2003	1	Atomic layer deposition for fabricating	438/14	257/E21.2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030	
3	<input type="checkbox"/>	Min, Yo Se	US 666999	2003	1	Atomic layer deposition method using	427/25	427/255.3		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 66699	
4	<input type="checkbox"/>	Rausch, W	US 200402	2004	1	Method of forming precision recessed	438/19	438/482		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
5	<input type="checkbox"/>	Aoyama, S	US 200402	2004	5	Method and device for processing sub	438/88			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
6	<input type="checkbox"/>	Conley, Jo	US 200402	2004	1	Modulated temperature method of ato	438/77	438/782		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
7	<input type="checkbox"/>	Yeo, Yee-C	US 200401	2004	1	Semiconductor chip with gate dielectri	257/50			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
8	<input type="checkbox"/>	Bude, Jeff	US 200401	2004	3	Semiconductor devices with reduced	438/93	257/431		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
9	<input type="checkbox"/>	Jang, Chuc	US 200400	2004	1	Atomic layer deposition of interpoly oxi	257/31	257/E21.2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	
10	<input type="checkbox"/>	Lee, Yun-J	US 200400	2004	2	Method of forming oxide layer using at	438/75	257/E21.2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040	